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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re the patent of:

KONNO et al.

Patent Number: 5,397,432

Issued: March 14, 1995

For: METHOD FOR PRODUCING SEMICONDUCTOR INTEGRATED CIRCUITS AND
APPARATUS USED IN SUCH METHOD

REQUEST FOR CERTIFICATE OF CORRECTION

Assistant Commissioner
for Patents

Washington, D.C. 20231

March 10, 1997

CERTIFICATE

APR 10 1997

Sir:

The undersigned requests that a Certificate of Correction be issued for the
above-identified patent as indicated on the attached Form PTO-1050.

REMARKS

This request is being made in order to correct our typographical error in
column 11, line 39 and the omission of symbols in Table-1. In support of the corrections
to Table-1, we are enclosing a copy of page 24 of the specification.

It is respectfully submitted that no new matter has been added.

Enclosed is a check for One Hundred Dollars (\$100.00) to cover any
necessary cost for this change. If however, any additional fees are due, please charge our
Deposit Account No. 14-1060.

Respectfully submitted,

NIKAIDO, MARMELSTEIN, MURRAY & ORAM LLP

George E. Oram, Jr.
Reg. No. 27,931

Atty. Case No. P698-1333

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2 145 100.00 CK

Enclosures: PTO Form 1050; Copy of Page 24 of the Specification; Check # 12856

18
E.J.



Table 1

Conditions	Amount of residual chlorine $\mu\text{m g/cm}^2$ 10^{15}atoms/cm^2		After- corrosion	Symbols shown in Fig. 9
① Etching only	0.92±0.06	16.0±1.0	Large	○
② Downflow ashing using O ₂ after ①	0.89±0.06	15.5±1.0	Large	●
③ Downflow ashing using O ₂ +CF ₄ after ①	0.54±0.03	9.3±0.4	Small	■
④ Downflow ashing using O ₂ +H ₂ O after ①	0.23±0.03	4.0±0.5	No	◇
⑤ Exposure to H ₂ O after ② (30sec)	0.51±0.02	8.7±0.3	Small	▲
⑥ Exposure to H ₂ O after ② (90sec)	0.48±0.01	8.1±0.2	Small	▲
⑦ Exposure to H ₂ O after ② (180sec)	0.45±0.04	7.6±0.7	Small	▲
⑧ Downflow treatment using H ₂ O after ② (30sec)	0.28±0.01	4.7±0.2	None	△
⑨ Downflow treatment using H ₂ O after ② (90sec)	0.15±0.00	2.5±0.0	No	△
⑩ Downflow treatment using H ₂ O after ② (180sec)	0.11±0.01	1.9±0.1	No	△
⑪ Downflow treatment using H ₂ after ② (30sec)	0.68±0.01	11.8±0.2	Small	▼
⑫ Downflow treatment using H ₂ O after ② (90sec)	0.68±0.01	11.7±0.1	Small	▼
⑬ Downflow treatment using H ₂ after ② (180sec)	0.64±0.01	11.1±0.2	Small	▼

Exposure to H₂O: heated at 120°C in water vapor at 0.1 Torr.

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PATENT AND TRADEMARK OFFICE

UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 5,397,432
DATED : March 14, 1995
INVENTOR(S) : KONNO et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 11, line 39, delete "or" insert therefor -- and -- *A*

5,397,432

MAILING ADDRESS OF SENDER:

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PATENT NO. _____

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Table - 1 insert symbols

Conditions	Amount of residual chlorine umg/cm ² · 10 ¹⁵ atoms/cm ²		After- corrosion	Symbols shown in FIG. 9
① Etching only	0.92±0.06	16.0±1.0	Large	○
② Downflow ashing using O ₂ after ①	0.39±0.06	15.5±1.0	Large	●
③ Downflow ashing using O ₂ +CF ₄ after ①	0.54±0.03	9.3±0.4	Small	■
④ Downflow ashing using O ₂ +H ₂ O after ①	0.23±0.03	4.0±0.5	No	◇
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Exposure to H₂O: heated at 120° C. in water vapor at 0.1 Torr.

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Conditions	Amount of residual chlorine umg/cm ² 10 ¹⁵ atoms/cm ²		After- corrosion	Symbols shown in FIG. 9
① Etching only	0.32±0.06	16.0±1.0	Large	○
② Downflow ashing using O ₂ after ①	0.39±0.06	15.3±1.0	Large	●
③ Downflow ashing using O ₂ +CF ₄ after ①	0.54±0.03	9.3±0.4	Small	■
④ Downflow ashing using O ₂ +H ₂ O after ①	0.23±0.03	4.0±0.5	No	◇
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